

**RADIATION HARDENED
 NPN SILICON SWITCHING TRANSISTOR**
Qualified per MIL-PRF-19500/255

DEVICES

| | |
|-------------------|-------------------|
| 2N2221A | 2N2222A |
| 2N2221AL | 2N2222AL |
| 2N2221AUA | 2N2222AUA |
| 2N2221AUB | 2N2222AUB |
| 2N2221AUBC | 2N2222AUBC |

LEVELS

- JANSM – 3K Rads (Si)**
- JANSD – 10K Rads (Si)**
- JANSP – 30K Rads (Si)**
- JANSL – 50K Rads (Si)**
- JANSR – 100K Rads (Si)**
- JANSF – 300K Rads (Si)**
- JANSG – 500K Rads (Si)**
- JANSH – 1MEG Rads (Si)**

ABSOLUTE MAXIMUM RATINGS (T_C = +25°C unless otherwise noted)

| Parameters / Test Conditions | Symbol | Value | Unit |
|--------------------------------------------------|------------------------------------|-------------|------|
| Collector-Emitter Voltage | V _{CEO} | 50 | Vdc |
| Collector-Base Voltage | V _{CBO} | 75 | Vdc |
| Emitter-Base Voltage | V _{EBO} | 6.0 | Vdc |
| Collector Current | I _C | 800 | mAdc |
| Total Power Dissipation @ T _A = +25°C | | | |
| 2N2221A, L 2N2222A, L | P _T | 0.5 | W |
| 2N2221AUA 2N2222AUA | | 0.65 | |
| 2N2221AUB, UBC 2N2222AUB, UBC | | 0.50 | |
| Operating & Storage Junction Temperature Range | T _{op} , T _{stg} | -65 to +200 | °C |

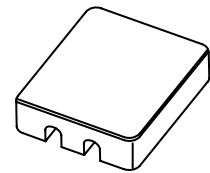
THERMAL CHARACTERISTICS

| Parameters / Test Conditions | Symbol | Max. | Unit |
|-----------------------------------------|------------------|------|------|
| Thermal Resistance, Junction-to-Ambient | | | |
| 2N2221A, L 2N2222A, L | R _{θJA} | 325 | °C/W |
| 2N2221AUA 2N2222AUA | | 210 | |
| 2N2221AUB, UBC 2N2222AUB, UBC | | 325 | |

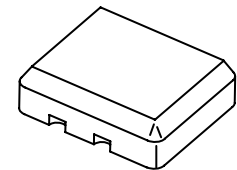
- Derate linearly 3.08 mW/°C above T_A > +37.5°C
- Derate linearly 4.76 mW/°C above T_A > +63.5°C



TO-18 (TO-206AA)
 2N2221A, 2N2222A



4 PIN
 2N2221AUA, 2N2222AUA



3 PIN
 2N2221AUB, 2N2222AUB
 2N2221AUBC, 2N2222AUBC
 (UBC = Ceramic Lid Version)

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
|----------------------------------------------------------------------------------------------------------------------------------|---------------|-----------|------------|-------------------------------------|
| OFF CHARACTERISTICS | | | | |
| Collector-Emitter Breakdown Voltage $I_C = 10\text{mA}$ | $V_{(BR)CEO}$ | 50 | | Vdc |
| Collector-Base Cutoff Current $V_{CB} = 75\text{Vdc}$ $V_{CB} = 60\text{Vdc}$ | I_{CBO} | | 10 10 | μAdc ηAdc |
| Emitter-Base Cutoff Current $V_{EB} = 6.0\text{Vdc}$ $V_{EB} = 4.0\text{Vdc}$ | I_{EBO} | | 10 10 | μAdc ηAdc |
| Collector-Emitter Cutoff Current $V_{CE} = 50\text{Vdc}$ | I_{CES} | | 50 | ηAdc |
| ON CHARACTERISTICS ⁽³⁾ | | | | |
| Forward-Current Transfer Ratio $I_C = 0.1\text{mA}$, $V_{CE} = 10\text{Vdc}$ | | 30 50 | | |
| | | | | |
| $I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$ | | 35 75 | 150 325 | |
| | | | | |
| $I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$ | h_{FE} | 40 100 | | |
| | | | | |
| $I_C = 150\text{mA}$, $V_{CE} = 10\text{Vdc}$ | | 40 100 | 120 300 | |
| | | | | |
| $I_C = 500\text{mA}$, $V_{CE} = 10\text{Vdc}$ | | 20 30 | | |
| | | | | |
| Collector-Emitter Saturation Voltage $I_C = 150\text{mA}$, $I_B = 15\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$ | $V_{CE(sat)}$ | | 0.3 1.0 | Vdc |
| | | | | |
| Base-Emitter Voltage $I_C = 150\text{mA}$, $I_B = 15\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$ | $V_{BE(sat)}$ | 0.6 | 1.2 2.0 | Vdc |
| | | | | |

DYNAMIC CHARACTERISTICS

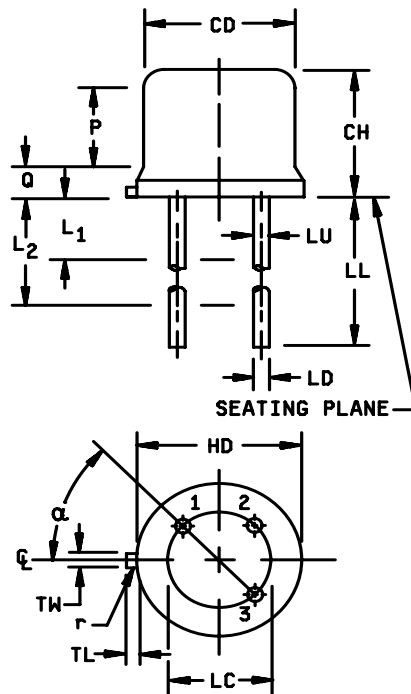
| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------|----------|------|------|
| Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, $f = 1.0\text{kHz}$ 2N2221A, L, UA, UB, UBC 2N2222A, L, UA, UB, UBC | h_{fe} | 30 50 | | |
| Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 20\text{mA}$, $V_{CE} = 20\text{Vdc}$, $f = 100\text{MHz}$ | $ h_{fe} $ | 2.5 | | |
| Output Capacitance $V_{CB} = 10\text{Vdc}$, $I_E = 0$, $100\text{kHz} \leq f \leq 1.0\text{MHz}$ | C_{obo} | | 8.0 | pF |
| Input Capacitance $V_{EB} = 0.5\text{Vdc}$, $I_C = 0$, $100\text{kHz} \leq f \leq 1.0\text{MHz}$ | C_{ibo} | | 25 | pF |

SWITCHING CHARACTERISTICS

| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
|----------------------------------------------------|-----------|------|------|------|
| Turn-On Time See figure 8 of MIL-PRF-19500/255 | t_{on} | | 35 | ns |
| Turn-Off Time See Figure 9 of MIL-PRF-19500/255 | t_{off} | | 300 | ns |

(3) Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

PACKAGE DIMENSIONS

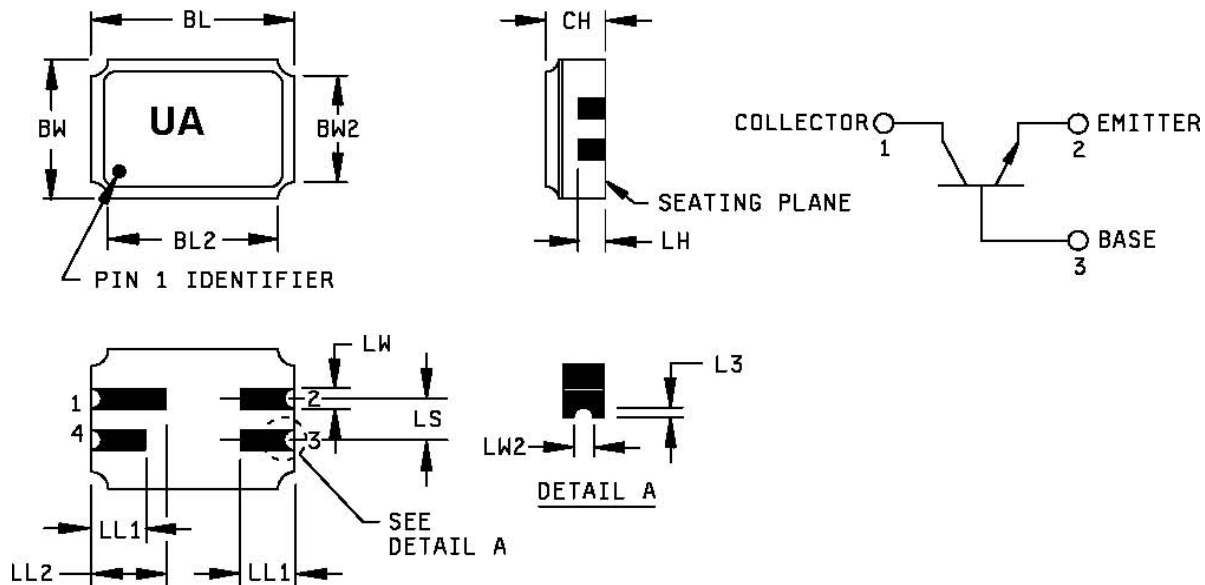


NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TL shall be held for a minimum length of .011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane $.054 +.001 - .000$ inch ($1.37 +0.03 -0.00$ mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
7. Dimension LU applies between L_1 and L_2 . Dimension LD applies between L_2 and LL minimum. Diameter is uncontrolled in L_1 and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension r (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.
12. Lead 1 = emitter, lead 2 = base, lead 3 = collector.
13. For L suffix devices, dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max.

| Symbol | Dimensions | | | | Note |
|---------------------|------------|------|-------------|-------|--------|
| | Inches | | Millimeters | | |
| | Min | Max | Min | Max | |
| CD | .178 | .195 | 4.52 | 4.95 | |
| CH | .170 | .210 | 4.32 | 5.33 | |
| HD | .209 | .230 | 5.31 | 5.84 | |
| LC | .100 TP | | 2.54 TP | | 6 |
| LD | .016 | .021 | 0.41 | 0.53 | 7,8 |
| LL | .500 | .750 | 12.70 | 19.05 | 7,8,13 |
| LU | .016 | .019 | 0.41 | 0.48 | 7,8 |
| L_1 | | .050 | | 1.27 | 7,8 |
| L_2 | .250 | | 6.35 | | 7,8 |
| P | .100 | | 2.54 | | |
| Q | | .030 | | 0.76 | 5 |
| TL | .028 | .048 | 0.71 | 1.22 | 3,4 |
| TW | .036 | .046 | 0.91 | 1.17 | 3 |
| r | | .010 | | 0.25 | 10 |
| α | 45° TP | | 45° TP | | 6 |
| 1, 2, 9, 11, 12, 13 | | | | | |

FIGURE 1. Physical dimensions (similar to TO-18).



NOTES:

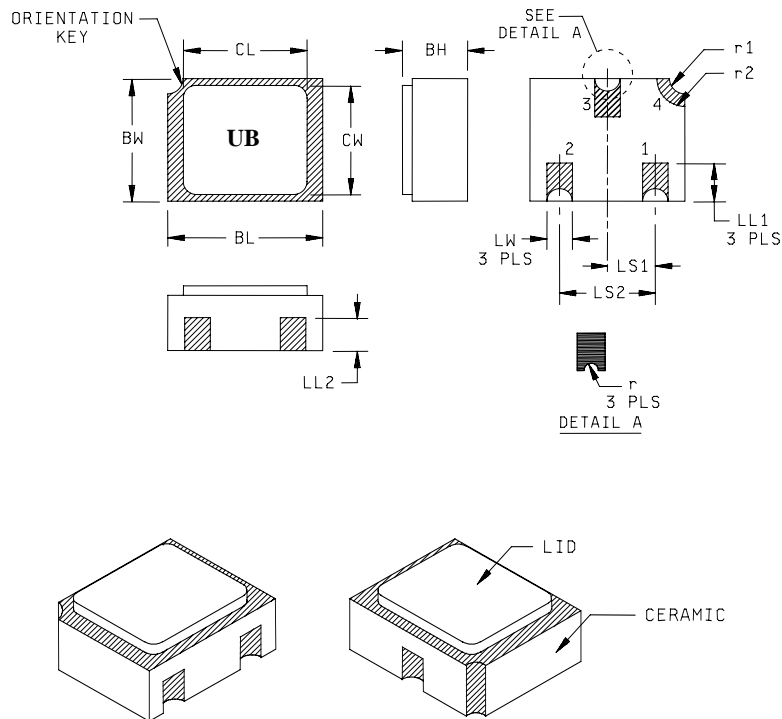
1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimension CH controls the overall package thickness. When a window lid is used, dimension CH must increase by a minimum of .010 inch (0.254 mm) and a maximum of .040 inch (1.020 mm).
4. The corner shape (square, notch, radius) may vary at the manufacturer's option, from that shown on the drawing.
5. Dimensions LW2 minimum and L3 minimum and the appropriate castellation length define an unobstructed three-dimensional space traversing all of the ceramic layers in which a castellation was designed. (Castellations are required on the bottom two layers, optional on the top ceramic layer.) Dimension LW2 maximum and L3 maximum define the maximum width and depth of the castellation at any point on its surface. Measurement of these dimensions may be made prior to solder dipping.
6. The co-planarity deviation of all terminal contact points, as defined by the device seating plane, shall not exceed .006 inch (0.15mm) for solder dipped leadless chip carriers.
7. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

| Symbol | Dimensions | | | | Note |
|--------|------------|------|-------------|------|------|
| | Inches | | Millimeters | | |
| | Min | Max | Min | Max | |
| BL | .215 | .225 | 5.46 | 5.71 | |
| BL2 | | .225 | | 5.71 | |
| BW | .145 | .155 | 3.68 | 3.93 | |
| BW2 | | .155 | | 3.93 | |
| CH | .061 | .075 | 1.55 | 1.90 | 3 |
| L3 | .003 | .007 | 0.08 | 0.18 | 5 |
| LH | .029 | .042 | 0.74 | 1.07 | |
| LL1 | .032 | .048 | 0.81 | 1.22 | |
| LL2 | .072 | .088 | 1.83 | 2.23 | |
| LS | .045 | .055 | 1.14 | 1.39 | |
| LW | .022 | .028 | 0.56 | 0.71 | |
| LW2 | .006 | .022 | 0.15 | 0.56 | 5 |

| Pin no. | 1 | 2 | 3 | 4 |
|------------|-----------|---------|------|-----|
| Transistor | Collector | Emitter | Base | N/C |

FIGURE 2. Physical dimensions, surface mount (UA version).

6 Lake Street, Lawrence, MA 01841
 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803
 Website: <http://www.microsemi.com>



| Symbol | Dimensions | | | | Note |
|--------|------------|------|-------------|------|------|
| | Inches | | Millimeters | | |
| | Min | Max | Min | Max | |
| BH | .046 | .056 | 1.17 | 1.42 | |
| BL | .115 | .128 | 2.92 | 3.25 | |
| BW | .085 | .108 | 2.16 | 2.74 | |
| CL | | .128 | | 3.25 | |
| CW | | .108 | | 2.74 | |
| LL1 | .022 | .038 | 0.56 | 0.96 | |
| LL2 | .017 | .035 | 0.43 | 0.89 | |

| Symbol | Dimensions | | | | Note |
|-----------------|------------|------|-------------|------|------|
| | Inches | | Millimeters | | |
| | Min | Max | Min | Max | |
| LS ₁ | .036 | .040 | 0.91 | 1.02 | |
| LS ₂ | .071 | .079 | 1.81 | 2.01 | |
| LW | .016 | .024 | 0.41 | 0.61 | |
| r | | .008 | | .203 | |
| r ₁ | | .012 | | .305 | |
| r ₂ | | .022 | | .559 | |

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Hatched areas on package denote metalized areas.
4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
5. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

FIGURE 3. Physical dimensions, surface mount (UB version)